

# DIGITRON SEMICONDUCTORS

## Rectifier Diodes

All parts are screened per MIL-PRF-19500, JANTX Level and the device detail specification. All testing is performed at room temperature, unless indicated otherwise. For testing at high and low temperatures, Group A testing is required.

	Test	Method	Conditions / Notes
1	Temperature Cycling	MIL-STD-750 Method 1051	Test condition C or maximum storage temperature, whichever less. 20 cycles, 10 minutes per extreme.
2	Surge Test	MIL-STD-750 Method 4066	Rated $I_{FSM}$ as specified in the detail drawing.
3	Thermal Impedance	MIL-STD-750 Method 3101	As specified in the detail drawing.
4	High Temperature Reverse Bias Burn-in (HTRB)	MIL-STD-750 Method 1038	Condition A. 80% of rated $V_R$ for 48 hours at 150°C.
5	Interim Electrical Testing		DC parameters per device detail specification.
6	Power Burn-in	MIL-STD-750 Method 1038	96 hours of forward bias per device detail specification.
7	Final Electrical Testing		DC parameters per device detail specification.
8	Delta Calculation		Delta parameters and limits per device detail specification.
9	PDA Calculation		10 percent defective allowed.
10	Seal Test Gross Leak	MIL-STD-750 Method 1071	Condition C

### Notes:

1. Testing varies in accordance with the device detail specification.
2. Specific customer testing needs may be accommodated into any testing flow (selection tests, temperature requirements, special tests).